

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|-------|------------------|---------|------------------|
| L1    | 1    | ("6818948").PN.  | USPAT | OR               | OFF     | 2005/03/31 10:54 |
| L2    | 1    | ("6093606").PN.  | USPAT | OR               | OFF     | 2005/03/31 10:54 |
| L3    | 1    | 1 and (trench or long or parallel or tunnel or oxide or isolation or source or drain or polysilicon or control or gate or plurality or pair or floating or region or electrically or bottom or memory or cell or side or wall or spacer or silicon or nitride or pad or shallow or dielectric or insulating or cvd or cmp or etch or etching or RTA) | USPAT | OR               | ON      | 2005/03/31 10:54 |
| L4    | 1    | 2 and (trench or long or parallel or tunnel or oxide or isolation or source or drain or polysilicon or control or gate or plurality or pair or floating or region or electrically or bottom or memory or cell or side or wall or spacer or silicon or nitride or pad or shallow or dielectric or insulating or cvd or cmp or etch or etching or RTA) | USPAT | OR               | ON      | 2005/03/31 10:54 |
| L5    | 2460 | 438/257  | USPAT | OR               | ON      | 2005/03/31 10:55 |
| L6    | 916  | 438/259  | USPAT | OR               | ON      | 2005/03/31 10:55 |
| L7    | 551  | 438/263  | USPAT | OR               | ON      | 2005/03/31 10:55 |
| L8    | 1310 | 438/264  | USPAT | OR               | ON      | 2005/03/31 10:55 |
| L9    | 534  | 438/267  | USPAT | OR               | ON      | 2005/03/31 10:55 |
| L10   | 965  | 438/270  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L11   | 795  | 438/286  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L12   | 836  | 438/289  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L13   | 1121 | 438/680  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L14   | 563  | 438/681  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L15   | 1141 | 438/689  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L16   | 3365 | 438/692  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L17   | 1446 | 438/700  | USPAT | OR               | ON      | 2005/03/31 10:56 |
| L18   | 381  | 438/663  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L19   | 519  | 438/589  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L20   | 641  | 438/593  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L21   | 1848 | 438/706  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L22   | 228  | 438/733  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L23   | 964  | 438/738  | USPAT | OR               | ON      | 2005/03/31 10:57 |
| L24   | 1466 | 438/745  | USPAT | OR               | ON      | 2005/03/31 10:57 |

|          |    |   |       |    |    |                  |
|----------|----|---|-------|----|----|------------------|
| S47<br>7 | 16 | (stacked adj gate adj flash adj<br>memory adj device)   | USPAT | OR | ON | 2005/03/31 09:37 |
| S47<br>8 | 4  | S477 and (trench and long and<br>parallel and tunnel and oxide and<br>isolation and source and drain and<br>polysilicon and control and gate<br>and plurality)  | USPAT | OR | ON | 2005/03/31 09:39 |
| S47<br>9 | 4  | S477 and (trench and long and<br>parallel and tunnel and oxide and<br>isolation and source and drain and<br>polysilicon and control and gate<br>and plurality and pair and floating<br>and region)  | USPAT | OR | ON | 2005/03/31 09:46 |
| S48<br>0 | 16 | S477 and (trench or long or<br>parallel or tunnel or oxide or<br>isolation or source or drain or<br>polysilicon or control or gate or<br>plurality or pair or floating or<br>region or electrically or bottom or<br>memory or cell or side or wall or<br>spacer or silicon or nitride or pad<br>or shallow or dielectric or<br>insulating or cvd or cmp or etch or<br>etching or RTA) | USPAT | OR | ON | 2005/03/31 10:54 |